

<b>Notice of References Cited</b>	Application/Control No. 10/710,724	Applicant(s)/Patent Under Reexamination KANG ET AL.	
	Examiner Russell M. Kobert	Art Unit 2829	Page 1 of 1

U.S. PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
*	A	US-4,542,340	09-1985	Chakravarti et al.	324/769
*	B	US-6,326,792	12-2001	Okada, Kenji	324/456
	C	US-			
	D	US-			
	E	US-			
	F	US-			
	G	US-			
	H	US-			
	I	US-			
	J	US-			
	K	US-			
	L	US-			
	M	US-			

FOREIGN PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
	N					
	O					
	P					
	Q					
	R					
	S					
	T					

NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	S. Satoh et al, "Stress Induced Leakage Current of Tunnel Oxide Derived From Flash Memory Read-Disturb Characteristics," March 1995, Proc. IEEE 1995 Int. Conference on Microelectronic Test Structures, Vol. 8, pages 97-101.
	V	Guoqiao Tao et al, "Fast wafer level monitoring of stress induced leakage current in deep sub-micron embedded non-volatile memory processes," 2002 (Month Unavailable), IEEE, 2002 IRW Final Report, pages 76-78.
	W	
	X	

\*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)  
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.